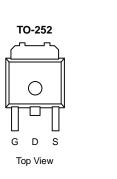
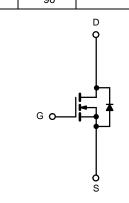


STD75N3LLH6-VB Datasheet N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Тур)			
30	0.002 at V _{GS} = 10 V	100	72 nC			
30	0.003 at V _{GS} = 4.5 V	90	72110			





N-Channel MOSFET

FEATURES

- ٠ Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU ٠

APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage		V _{GS}		± 20	
	T _C = 25 °C		100 ^{a, e}	A	
Continuous Drain Current (T _{.1} = 175 °C)	T _C = 70 °C		80 ^e		
Continuous Drain Current $(1_j = 175^{\circ} C)$	T _A = 25 °C	I _D	35.8 ^{b, c}		
	T _A = 70 °C		27 ^{b, c}		
Pulsed Drain Current	I _{DM}	300			
valanche Current Pulse		I _{AS}		39	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	94.8	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C	1	90 ^{a, e}		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	3.13 ^{b, c}	— A	
	T _C = 25 °C		235 ^a	w	
Maria Diana Diani ani	T _C = 70 °C	Р	165		
Maximum Power Dissipation	T _A = 25 °C	P _D	3.75 ^{b, c}		
	T _A = 70 °C		2.63 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Тур.	Max.	Unit		
Maximum Junction-to-Ambient ^{b, d}	$t \le 10 \text{ sec}$	R _{thJA}	32	40	°C/W		
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	0/10		

Notes:

a. Based on T_C = 25 °C. b. Surface mounted on 1" x 1" FR4 board.

a. t = 10 sec.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•		•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$		- 7.5		mv/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.5		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Maltana Duain Cumant	1	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	30 30 35 -7.5 1.5 -7.5 1.5 90 90 90 90 90 90 1002 90 150 151 770 151 71.5 30 24 1.4 18 11 70 10 55 180 55 12 12 0.8 52 70.2	10	μA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	90			A	
		V _{GS} = 10 V, I _D = 38.8 A		0.002			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 37 \text{ A}$		0.003		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 38.8 A		160		S	
Dynamic ^b					I	1	
Input Capacitance	C _{iss}			5201			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1525		pF	
Reverse Transfer Capacitance	C _{rss}			770			
T () Q ()	Qg	V_{DS} = 15 V, V_{GS} = 10 V, I_{D} = 38.8 A		151	227	nC	
Total Gate Charge				71.5	103		
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 28.8 A		30			
Gate-Drain Charge	Q _{gd}			24		1	
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}{\cong}\text{24}$ A, V_GEN = 10 V, R_g = 1 Ω		70	105		
Fall Time	t _f			10	15		
Turn-On Delay Time	t _{d(on)}			55	83	ns	
Rise Time	t _r	V_{DD} = 15 V, R _L = 0.67 Ω		180	270	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 22.5 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		55	83		
Fall Time	t _f			12	18	1	
Drain-Source Body Diode Characteristic	s				I		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	•	
Pulse Diode Forward Current ^a	I _{SM}				120	A	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC	
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		27			
Reverse Recovery Rise Time	t _b			25		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

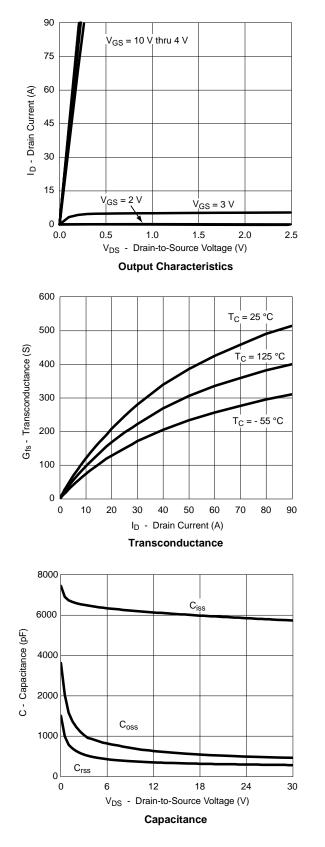
b. Guaranteed by design, not subject to production testing.

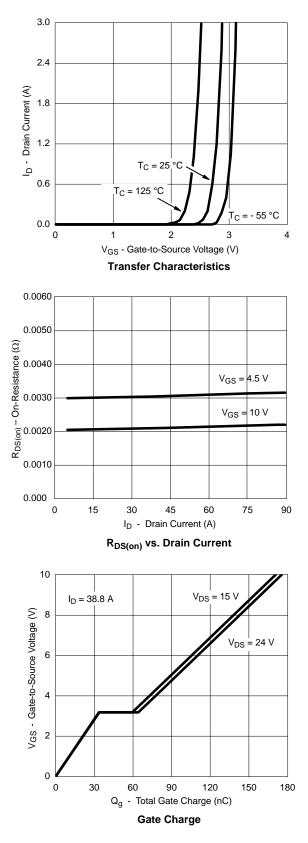
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Bsemi



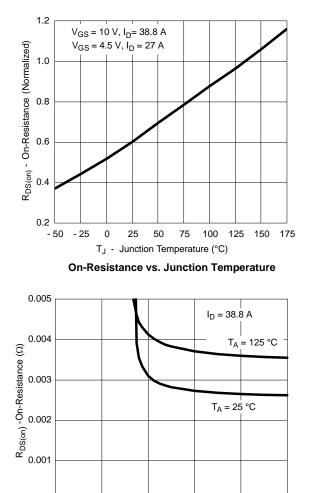
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

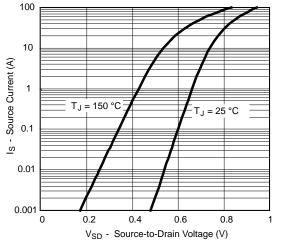




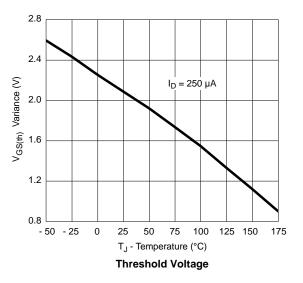


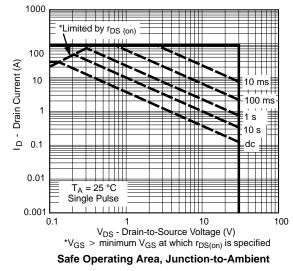
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Forward Diode Voltage vs. Temperature





0.000

0

2

4

6

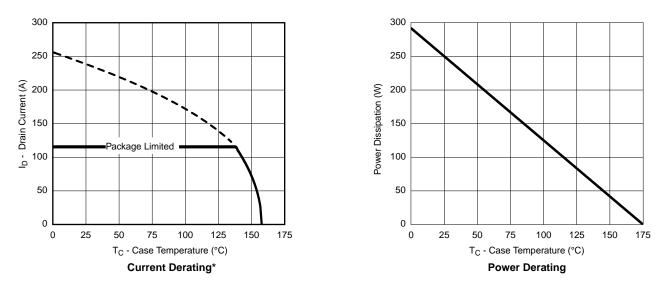
 V_{GS} - Gate-to-Source Voltage (V)

 $R_{DS(on)}$ vs. V_{GS} vs. Temperature

8

10





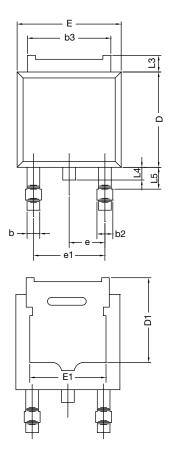
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

*The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





TO-252AA CASE OUTLINE





	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	2.28 BSC		BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.



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